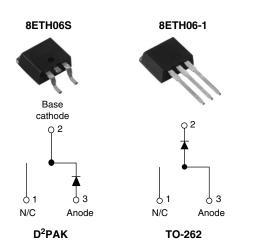


Vishay High Power Products

Hyperfast Rectifier, 8 A FRED Pt[™]



PRODUCT SUMMARY				
t _{rr} (typical)	18 ns			
I _{F(AV)}	8 A			
V _R	600 V			

FEATURES

- Hyperfast recovery time
- · Low forward voltage drop
- · Low leakage current
- 175 °C operating junction temperature
- Designed and qualified for industrial level

DESCRIPTION/APPLICATIONS

State of the art hyperfast recovery rectifiers designed with optimized performance of forward voltage drop, hyperfast recovery time, and soft recovery.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness and reliability characteristics.

These devices are intended for use in PFC boost stage in the AC-DC section of SMPS, inverters or as freewheeling diodes.

Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

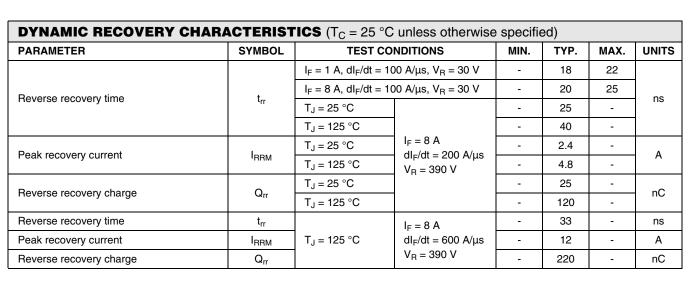
ABSOLUTE MAXIMUM RATINGS					
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS	
Peak repetitive reverse voltage	V _{RRM}		600	V	
Average rectified forward current	I _{F(AV)}	T _C = 144 °C	8		
Non-repetitive peak surge current	I _{FSM}	T _J = 25 °C	90	А	
Peak repetitive forward current	I _{FM}		16		
Operating junction and storage temperatures	T _J , T _{Stg}		- 65 to 175	°C	

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Breakdown voltage, blocking voltage	V _{BR} , V _R	I _R = 100 μA 600		-	-		
Forward voltage V _F	V	I _F = 8 A	-	2.0	2.4	V	
	۷F	I _F = 8 A, T _J = 150 °C	-	1.3	1.8		
Reverse leakage current I _R	$V_{R} = V_{R}$ rated	-	0.3	50			
	IR	$T_J = 150 \ ^{\circ}C, \ V_R = V_R \ rated$	-	55	500	μΑ	
Junction capacitance	CT	V _R = 600 V	-	17	-	pF	
Series inductance	L _S	Measured lead to lead 5 mm from package body	-	8.0	-	nH	

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THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Maximum junction and storage temperature range	T _J , T _{Stg}		- 65	-	175	°C
Thermal resistance, junction to case per leg	R _{thJC}		-	1.4	2	
Thermal resistance, junction to ambient per leg	R _{thJA}	Typical socket mount	-	-	70	°C/W
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth and greased	-	0.5	-	
Weight			-	2.0	-	g
			-	0.07	-	OZ.
Mounting torque			6.0 (5.0)	-	12 (10)	kgf ⋅ cm (lbf ⋅ in)
		Case style D ² PAK	8ETH06S			
Marking device		Case style TO-262	8ETH06-1			

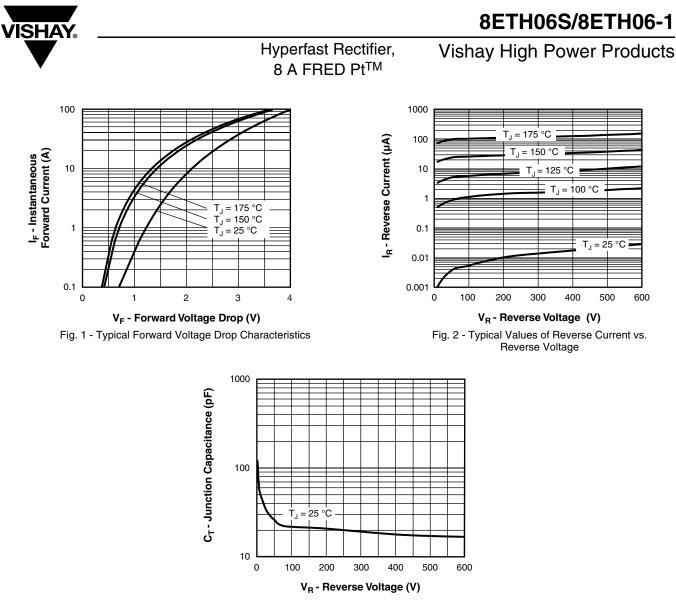


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

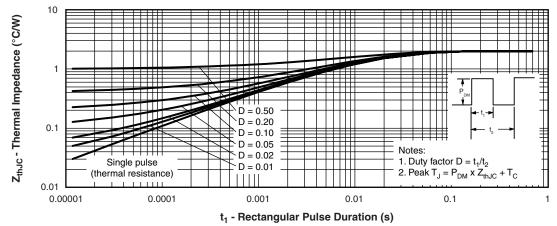


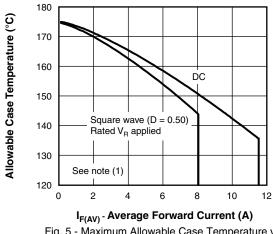
Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

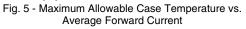
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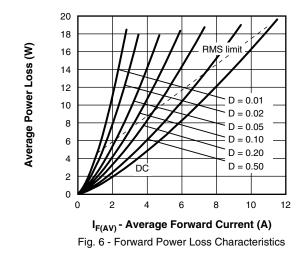
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Note

- ⁽¹⁾ Formula used: $T_C = T_J (Pd + Pd_{REV}) \times R_{thJC}$;
- $\begin{array}{l} \mathsf{Pd} = \mathsf{Forward} \ \mathsf{power} \ \mathsf{loss} = \mathsf{I}_{\mathsf{F}(\mathsf{AV})} \ \mathsf{x} \ \mathsf{V}_{\mathsf{FM}} \ \mathsf{at} \ (\mathsf{I}_{\mathsf{F}(\mathsf{AV})}/\mathsf{D}) \ (\mathsf{see} \ \mathsf{fig.} \ \mathsf{6}); \\ \mathsf{Pd}_{\mathsf{REV}} = \mathsf{Inverse} \ \mathsf{power} \ \mathsf{loss} = \mathsf{V}_{\mathsf{R1}} \ \mathsf{x} \ \mathsf{I}_{\mathsf{R}} \ (\mathsf{1} \mathsf{D}); \ \mathsf{I}_{\mathsf{R}} \ \mathsf{at} \ \mathsf{V}_{\mathsf{R1}} = \mathsf{Rated} \ \mathsf{V}_{\mathsf{R}} \end{array}$

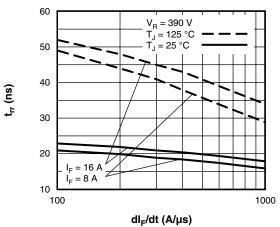
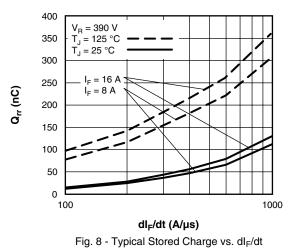


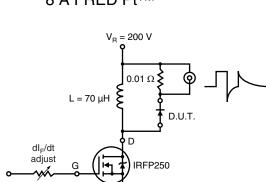
Fig. 7 - Typical Reverse Recovery Time vs. dl_F/dt





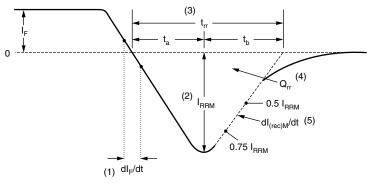
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Fig. 9 - Reverse Recovery Parameter Test Circuit



(1) dI_F/dt - rate of change of current through zero crossing

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(4) Q_{rr} - area under curve defined by t_{rr} and I_{RRM}

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

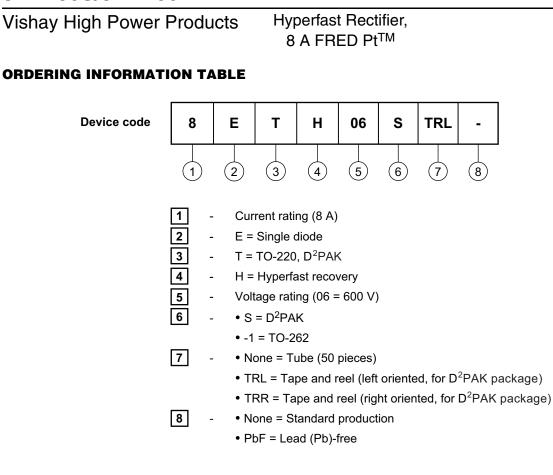
(2) I_{RRM} - peak reverse recovery current (3) $t_{\rm rr}$ - reverse recovery time measured from zero crossing point of negative

going I_F to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current.

(5) $dI_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

Fig. 10 - Reverse Recovery Waveform and Definitions

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LINKS TO RELATED DOCUMENTS				
Dimensions http://www.vishay.com/doc?95014				
Part marking information	http://www.vishay.com/doc?95008			
Packaging information	http://www.vishay.com/doc?95032			



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